

Electronic structures of (In,Ga)As/GaAs quantum dot molecules made of dots with dissimilar sizes

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... $\text{-QDM } M$...
 M ... S ...

$$-\frac{1}{2}\nabla^2 + V_{\vec{r}} \quad i \mathbf{r} = i i \mathbf{r}, \quad (1)$$

... $V_{\vec{r}}$... $V_{\vec{r}} \mathbf{r} = n, v \mathbf{r}$...
 $-R_n + V_{\vec{r}} \cdot \mathbf{I} \dots R_n \dots$
 $\dots = I, G, A_{\vec{r}} \dots$
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$$H = \hat{p}_i \hat{p}_i$$

$$\frac{t}{t_w} = \frac{t}{t_g} = \frac{t}{t_g} E_X = 1156 \mu_V$$

Sum of ... $2t M$... $2t M$
... H w , t -
... I A3/G A3 QDM,⁹ ...

$$= \begin{pmatrix} 0 & -e_3 & 0 & -e_1 \\ c_3 & 0 & c_2 & 0 \\ 0 & -e_2 & 0 & -e_4 \\ c_1 & 0 & c_4 & 0 \end{pmatrix} \quad 14$$

$$i, j = e_T^\dagger e$$

B. Degree of entanglement vs double occupation

E

$$|g\rangle = c_1 e_T^\dagger e_B^\dagger + c_2 e_B^\dagger e_T^\dagger + c_3 e_T^\dagger e_T^\dagger + c_4 e_B^\dagger e_B^\dagger$$

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$$c_1^2 + c_2^2 + c_3^2 + c_4^2 = 1. \text{ At } |g\rangle, w$$

$$|g\rangle = \sum_{ij} i \otimes j, \quad 13$$

